## Interm ediatevalencebehaviorin CeCo<sub>9</sub>Si<sub>4</sub>

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## A bstract

The noveltemary compound C 
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K ey words:

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The ordered temary rare-earth cobalt silicon phase with composition 1:9:4 attracted our attention mainly because of the extraordinary magnetic properties of LaCo $_9$ Si $_4$  which is a strongly exchange enhanced Pauli paramagnet and exhibits an itinerant metamagnetic phase transition at about 3.5 T for H jp and 6 T for H?c, which is the lowest value ever found for rare earth intermetallic compounds [1]. Related isostructural RCo $_9$ Si $_4$  with R = Pr, Nd, Gd, Dy and also Y are ferromagnetic (see Refs. [2,3]) with relatively low  $T_{\rm C}$  20 50 K. This report is on the exceptional behavior of CeCo $_9$ Si $_4$  among the ferromagnetic (FM) or almost FM RCo $_9$ Si $_4$  compounds.

Polycrystalline samples of  $C \in Co_9Si_4$  and related  $R Co_9Si_4$  were synthesized by induction melting of

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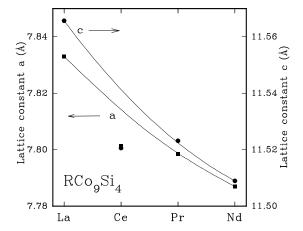


Fig. 1. Comparison of lattice parameters a (squares) and c (circles) of some RC  $o_9\,S\,i_4$  compounds; dashed lines guides to the eye.

pure elements (R 3N, Co 4.5N, Si 6N) under protective argon atmosphere and subsequent annealing at

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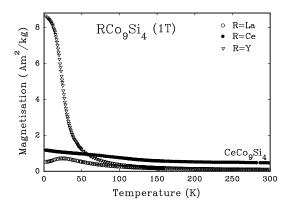


Fig.2.Tem perature dependent magnetisation M (T) measured at 1T of CeCo<sub>9</sub>Si<sub>4</sub> and for comparison LaCo<sub>9</sub>Si<sub>4</sub> and YCo<sub>9</sub>Si<sub>4</sub>.

1050 C for one week. The crystal structure was determ ined by means of single crystal X-ray diraction (R  $_{\rm F}$   $^2$  = 2.3%) revealing, analogous to CeN i\_9Si\_4 [4], a fully ordered distribution of Ce, Co and Si atoms with the LaFe\_9Si\_4-type [5] (space group I4-m cm). The lattice parameters are a = 7:801(1)A and c = 11:521(2)A at room temperature.

The comparison of the lattice parameters of RC og Si4 with R = La, Ce, Pr, Nd shown in Fig. 1 reveals a signi cant negative deviation of the CeCo, Si4 data from the common trend. The smaller lattice constants of CeCo<sub>2</sub>Si<sub>4</sub> indicates an intermediate valence state inbetween them agnetic trivalent  $4f^1$  and the non-magnetic tetravalent 4f° state due to hybridization of 4f and conduction band states. Interm ediate valence close to tetravalence is corroborated by the magnetisation data shown in Fig. 2 where the Curie-Weiss component expected for Ce3+ ions is not observed. The dc susceptibility measurement in fact reveals an almost temperature independent param agnetic susceptibility for CeCo<sub>9</sub>Si<sub>4</sub>, while LaCo<sub>9</sub>Si<sub>4</sub> exhibits a more pronounced tem perature dependence, typical for a spin uctuation system, and all other RCO9Si4 are ferrom agnetic below 20{50 K (see the Y C og Si4 data shown in Fig. 2 as one example). The smallo -set of the room temperature m agnetic m om ent of CeCo<sub>9</sub>Si<sub>4</sub> as compared with LaC o<sub>9</sub> Si<sub>4</sub> and Y C o<sub>9</sub> Si<sub>4</sub> in Fig. 2 is due to a contribution from traces of unreacted free Cowhich is also visible in the M (H) data (see Fig. 3). The Pauli-susceptibility  $_{0}$ estim ated from M =H at  $40 \,\mathrm{T}$  is about 5  $10^{-7} \,\mathrm{m}^{-3}/\mathrm{kg}$ , slightly sm aller than 8.2  $10^{-7}$  m  $^3/kg$  given in Ref. [1] for LaC og Si4.

M otivated by the metamagnetism observed for LaCo $_9$ Si $_4$  high-eld magnetisation M (H) measurements have been carried out up to 40 T in pulsed elds (see Ref.[6] for details of the setup) on CeCo $_9$ Si $_4$  and LaCo $_9$ Si $_4$  for comparison. Apart from a small hysteresis at low elds due to the above mentioned Co impurities, CeCo $_9$ Si $_4$  shows a rather perfectly linear

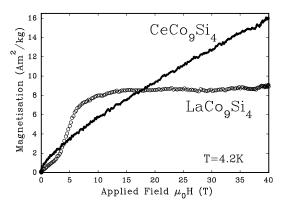


Fig. 3. High-eld magnetisation measurements M (H ) on CeCo $_9\,\mathrm{Si}_4$  and LaCo $_9\,\mathrm{Si}_4$  performed at  $4.2\,\mathrm{K}$  .

param agnetic eld dependence reaching 2  $_{\rm B}$  /fu. at B  $_{\rm m.a.x}$  = 40 T, whereas the magnetic moment of the eld induced FM state of LaC  $_{\rm OS}$  Si4 saturates already above about 8 T at approximately 1.1  $_{\rm B}$  /fu.

The obviously more stable param agnetic state of CeCo $_9$ Si $_4$  with respect to the appearance ofm etam agnetism is most likely due to d-band lling caused by hybridized 4f states of cerium being close to tetravalence. Thus, one expects a reduction of spin-uctuation mass enhancem ent which however may be partly compensated by contributions due to Ce valence uctuations. The latter is supported by the specic heat data (not shown) where the linear electronic specic heat coe cient of CeCo $_9$ Si $_4$ , the Som merfeld value 190 m J/m olK 2, is slightly lower than that of nearly magnetic LaCo $_9$ Si $_4$ , where 1200 m J/m olK 2. The comparison of the temperature dependent resistivities

(T), on the other hand (not shown), indicates for both a Fermiliquid behavior with (T) =  $_0$  + AT $^2$ , however, with a signicantly lower A-coe cient for CeC  $o_9$  Si $_4$  as compared to LaC  $o_9$  Si $_4$  [7].

We conclude that  $C \in C \circ_9 Si_4$  exhibits intermediate valence with  $C \circ_9 Si_4$  exhibits intermediate valence valen

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